IN THE CLAIMS:

The listing of claims replaces all prior versions, and listings, of claims in the application.

1. – 4. (Canceled)

5. (Currently Amended) ~~The method of claim 3,~~ A method, comprising:

forming source/drain regions on a substrate;

etching the source/drain regions to form faceted regions;

forming a silicon germanium layer on the faceted regions of the source/drain regions; and

depositing a silicon layer above the silicon germanium layer to form a strained device, wherein anisotropic wet etching allows for controlled faceting of the source/drain regions based on a crystal density and a crystal orientation of the source/drain regions.

6. (Canceled)

7. (Currently Amended) ~~The method of claim 4,~~ A method, comprising:

forming source/drain regions on a substrate;

anisotropic wet-etching the source/drain regions to form faceted regions;

forming a silicon germanium layer on the faceted regions of the source/drain regions, wherein the faceted regions have an etch-out angle of about 120 degrees to about 130 degrees.

8. (Canceled)

9. (Currently Amended) ~~The method of claim 8, wherein wet etching further comprises using an etch solution having about 2 percent to about 30 percent ammonium hydroxide by volume~~ A method, comprising:

wet etching a source/drain region of a substrate with an etch solution having about 2 percent to about 30 percent ammonium hydroxide by volume;

forming a facet region in the source/drain region;

layering the facet region with silicon germanium; and

depositing silicon above silicon germanium.

10. (Original) The method of claim 9, wherein the etch solution has a pH of about 9 to about 11.

11. (Original) The method of claim 10, wherein the etch solution has a temperature of about 15 ^{0}C to about 60 ^{0}C.

12. (Currently Amended) ~~The method of claim 8, wherein wet etching further comprises using an etch solution of about 10 percent to about 30 percent tetra methyl ammonium hydroxide by volume~~ A method, comprising:

wet etching a source/drain region of a substrate with an etch solution having about 10 percent to about 30 percent tetra methyl ammonium by volume;

forming a facet region in the source/drain region;

layering the facet region with silicon germanium; and

depositing silicon above silicon germanium.

13. (Original) The method of 12, wherein the etch solution has a temperature of about 20 ^{0}C to about 45 ^{0}C.

14. (Currently Amended) ~~The method of claim 8, wherein wet etching further comprises etching the source/drain region to an etch depth of about 100 Angstroms to about 500 Angstroms~~ A method, comprising:

wet etching a source/drain region of a substrate to an etch depth of about 100 Angstroms to about 500 Angstroms;

forming a facet region in the source/drain region;

layering the facet region with silicon germanium; and

depositing silicon above silicon germanium.

15. – 16. (Canceled)

17. (Original) The method of claim 9, wherein the etch solution is based on a crystal density and a crystal orientation of the substrate.

18. (Original) The method of claim 12, wherein the etch solution is based on a crystal density and a crystal orientation of the substrate.

19. (Original) The method of claim 12, wherein wet etching further comprises sonicating the wet etch solution.

20. – 21. (Canceled)

22. (Currently amended) ~~The method of claim 21, wherein etching further comprises wet etching with an etch solution of about 10 percent to about 30 percent tetra methyl ammonium hydroxide by volume~~ A method, comprising:

providing a substrate having a source/drain region, a gate electrode disposed above the substrate, and a channel region formed below the gate electrode;

etching the source/drain region to form a faceted region near the channel region with an etch solution of about 10 percent to about 30 percent tetra methyl ammonium hydroxide by volume;

layering the faceted region with silicon germanium; and

depositing silicon above the silicon germanium.

23. – 30. (Canceled)